Schottky barrier diode

RB531XN

●Applications

Rectifying small power

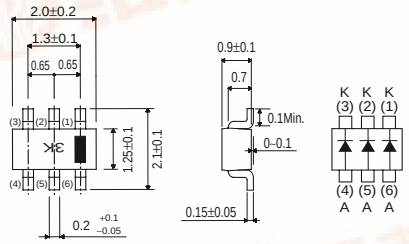
●Features

1) Small mold type. (UMD6)
2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



ROHM : UMD6
EIAJ : SOT-363
JEDEC :

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current *1	I_O	100	mA
Peak forward surge curren *2	I_{FSM}	1	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–40 to +125	°C

*1 Rating of per diode.
*2 60Hz for 1 ∿

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F1	–	–	0.300	V	I_F=10mA
	V_F2	–	–	0.430	V	I_F=100mA
Reverse current	I_R	–	–	20	µA	V_R=10V

Note) Please pay attention to static electricity when handling.

●**Electrical characteristic curves** (Ta=25°C)

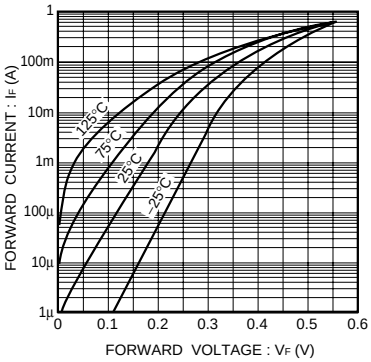


Fig.1 Forward characteristics

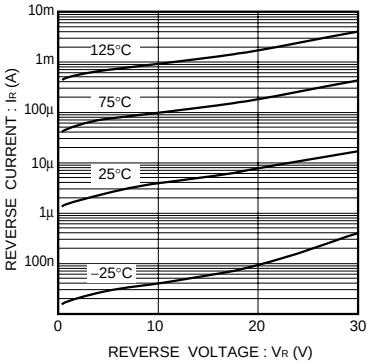


Fig.2 Reverse characteristics

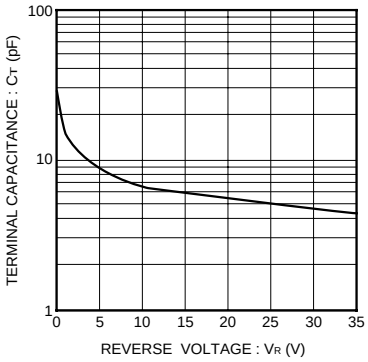


Fig.3 Capacitance between terminals characteristics